

Publications

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Conferences and Seminars

- DPG Tagung, Regensburg (Germany) 1996: Poster
Verhandlungen der Deutschen Physikalischen Gesellschaft, 24. DPG Tagung (1996)
- PHASDOM97, Aachen (Germany) 1997: Poster
Conference proceedings of the PHASDOM97, K. M. Indlekofer, J. Lange, A. Förster, H. Lüth, Aachen (1997)
- DPG Tagung, Regensburg (Germany) 1998: Oral presentation
Verhandlungen der Deutschen Physikalischen Gesellschaft, ISSN 0420-0195, 26. DPG Tagung HL29.3 (1998)
- PHASDOM98, Grenoble (Switzerland) 1998: Poster
Conference proceedings of the PHASDOM98, K. M. Indlekofer, A. Förster, H. Lüth
- Workshop on quantum transport in semiconductors, Maratea (Italy) 2001: contribution to talk given by J. P. Bird: “The metal-insulator transition in open quantum dots and arrays”
- HCIS-12, Santa Fe (NM, USA) 2001: Poster
K. M. Indlekofer, A. Förster, and H. Lüth, “Density-matrix description of a quantum dot system with lateral confinement in the single-electron tunneling regime”, *Physica B* 314, 499 (2002)
- Nitride Semiconductors – IWN2002, Aachen (Germany) 2002: Oral presentation
K. M. Indlekofer, E. Donà, J. Malindretos, M. Bertelli, M. Kočan, A. Rizzi, and H. Lüth, “Modelling of polarization charge induced asymmetry of IV-characteristics for AlN/GaN based Resonant Tunneling Structures”, *phys. stat. sol. (b)* 234 (2) 769-772 (2002)
- Hausseminar des IV. Physikalischen Instituts der Universität Göttingen (Institut für Halbleiterphysik), (December 12, 2002): Invited talk
K. M. Indlekofer, “Interaction Effects in Semiconductor Quantum Dot Systems”
- NanoMES, Tempe (AZ, USA) 2003: Oral presentation
K. M. Indlekofer, J. P. Bird, R. Akis, D. K. Ferry, and S. M. Goodnick, “A model for interaction corrections to transport through open quantum dots”, *Physica E* 19, 206-209 (2003)
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- Herbstschule in Riezlern (Austria) des IV. Physikalischen Instituts der Universität Göttingen, (September 20-26, 2003): Invited talk
K. M. Indlekofer, “Electronic Structure of Quantum Dots”
- 19th Umbrella Symposium, Nanotechnology, (March 1-3, 2004): Invited talk
K. M. Indlekofer, “Canonical Diagonalization for Few-Electron Nanosystems: Many-Body Coulomb Effects and THz Response”
- Seminarium z Fizyki Ciała Stałego, AGH Krakow (Poland), (November 17, 2004): Invited talk
K. M. Indlekofer, “Interaction effects in quantum dot systems”
- CNI-Seminar Forschungszentrum Jülich, (April 22, 2005), M. Indlekofer, “Quantum kinetic description of electronic transport in nanostructures”

- Seminar at the Slovak Academy of Sciences, Bratislava (November 3, 2005): Invited talk
K. M. Indlekofer, “Single-electron tunneling: technology, experiment, theory”
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- DPG Tagung, Dresden (Germany) 2006: Oral presentation
K. M. Indlekofer, “Simulation of electronic transport in nanoscale ferroelectric tunnel junctions”
Verhandlungen der Deutschen Physikalischen Gesellschaft, ISBN 2-914771-32-0, DF1.10 (2006)
- 64th Device Research Conference (DRC), Penn State University, USA, (Jun 25-28, 2006): Oral presentation
K. M. Indlekofer, J. Knoch, and J. Appenzeller, “Seamless transition from the single-electron regime to field-effect transistor operation of nanoscale Schottky-barrier FETs”, ISBN 1-4244-9749-5, IEEE Catalog Nr. 06TH8896, VI.B-4 (2006)
- Semiconductor Nanowire Symposium, Philips HighTech Campus Eindhoven, (September 19, 2006): Poster
K. M. Indlekofer and J. Knoch, “Simulation of Coulomb charging effects in nanowire-transistors”
- Programm-Beirat Jülich, (September 25, 2006): Oral presentation
K. M. Indlekofer, J. Wensorra, and M. Lepsa, “Quantum collimation in nanocolumns”
- Nanoelectronics Days 2006, RWTH Aachen, (October 11-13, 2006): Oral presentation
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- Joint meeting between ISIR SANKEN, Osaka University and the FZ Jülich on October 30, 2006 at Forschungszentrum Jülich: Invited talk
K. M. Indlekofer, “Quantum transport in semiconductor nanocolumns: Advanced Simulation Techniques”
- CNI-Seminar Forschungszentrum Jülich, (February 14, 2007), M. Indlekofer, “Simulation of many-body Coulomb effects in nanowire transistors”
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K. M. Indlekofer, J. Knoch, and J. Appenzeller, “Realistic simulation of nanowire transistors: A multi-configurational approach to Coulomb effects”
Verhandlungen der Deutschen Physikalischen Gesellschaft, ISSN 0420-0195, HL24.10 (2007)
- VISel Workshop Aachen 2007, (April 16-17, 2007): Invited talk
M. Indlekofer, “Coulomb blockade in gated nanowires”
- 65th Device Research Conference (DRC), University of Notre Dame, USA, (Jun 17-21, 2007): Oral presentation
K. M. Indlekofer, R. Németh, and J. Knoch, “THz probe for nanowire FETs: simulation of few-electron fingerprints”, ISBN 1-4244-1102-5, IEEE Catalog Nr. 07TH8948, IV.B-9 (2007)
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